

# 1N914(A)(B)

## 500mW 100 Volt Silicon Epitaxial Diode

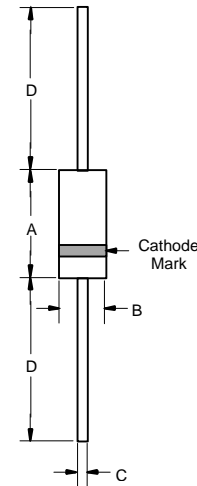
### Features

- Low Current Leakage
- Metalurgically Bonded Construction
- Low Cost

### Maximum Ratings

- Operating Temperature: -65°C to +175°C
- Storage Temperature: -65°C to +175°C
- Maximum Thermal Resistance; 35°C/W Junction To Ambient

### DO-35



### Electrical Characteristics @ 25°C Unless Otherwise Specified

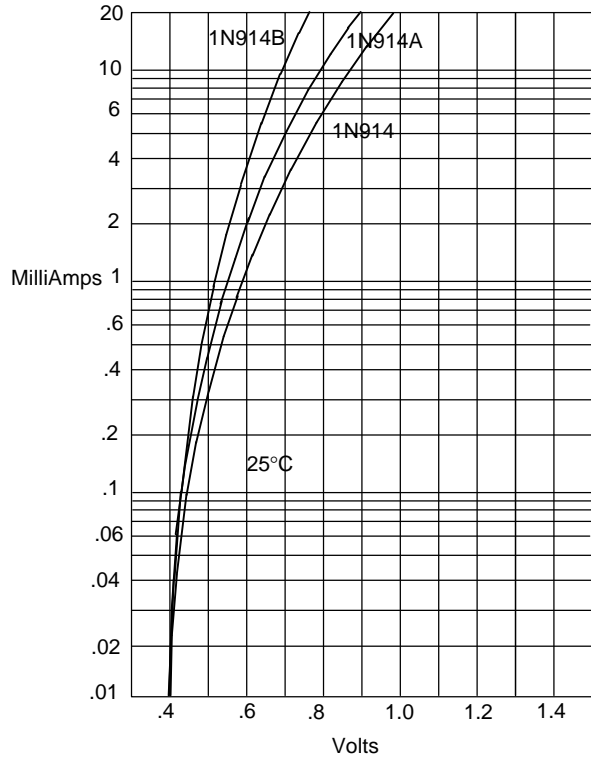
Reverse Voltage	$V_R$	75V	
Peak Reverse Voltage	$V_{RM}$	100V	
Average Rectified Current	$I_O$	150mA	Resistive Load $f > 50\text{Hz}$
Power Dissipation	$P_{TOT}$	500mW	
Junction Temperature	$T_J$	200°C	
Peak Forward Surge Current	$I_{FSM}$	500mA	8.3ms, half sine
Maximum Instantaneous Forward Voltage	$V_F$	1.0V	$I_{FM} = 10\text{mA};$ $T_J = 25^\circ\text{C}^*$
Maximum DC Reverse Current At Rated DC Blocking Voltage	$I_R$	25nA 50μA	$V_R=20\text{Volts}$ $T_J = 25^\circ\text{C}$ $T_J = 150^\circ\text{C}$
Typical Junction Capacitance	$C_J$	4pF	Measured at 1.0MHz, $V_R=4.0\text{V}$
Reverse Recovery Time	$T_{rr}$	4nS	$I_F=10\text{mA}$ $V_R = 6\text{V}$ $R_L=100\Omega$

\*Pulse test: Pulse width 300 μsec, Duty cycle 2%

DIM	DIMENSIONS				NOTE
	INCHES		MM		
	MIN	MAX	MIN	MAX	
A	---	.166	---	4.2	
B	---	.079	---	2.00	
C	---	.020	---	.52	
D	1.000	---	25.40	---	

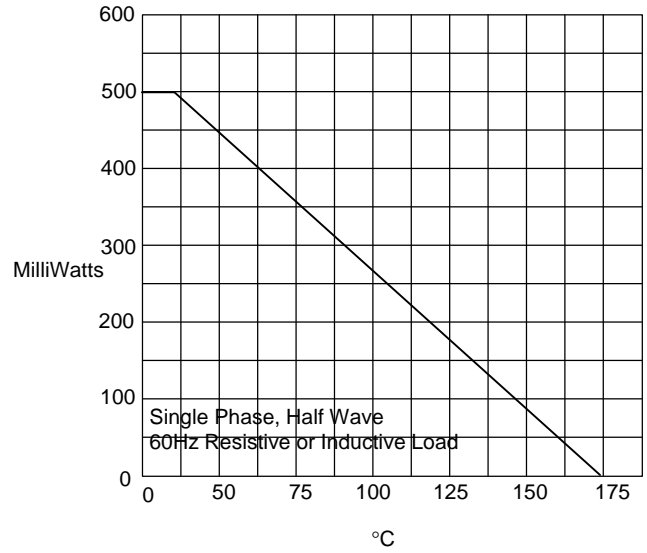
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Figure 1  
Typical Forward Characteristics



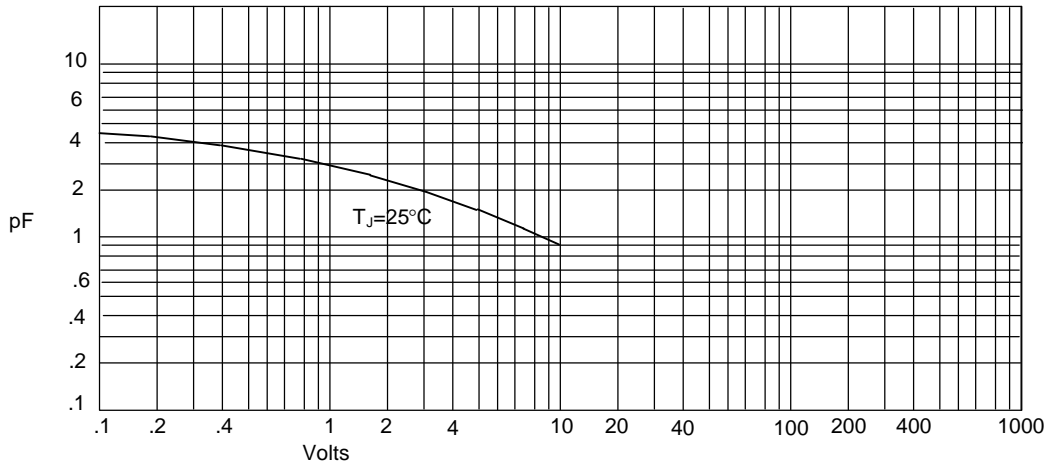
Instantaneous Forward Current - Amperes versus  
Instantaneous Forward Voltage - Volts

Figure 2  
Forward Derating Curve



Admissible Power Dissipation - MilliWatts versus  
Ambient Temperature - °C

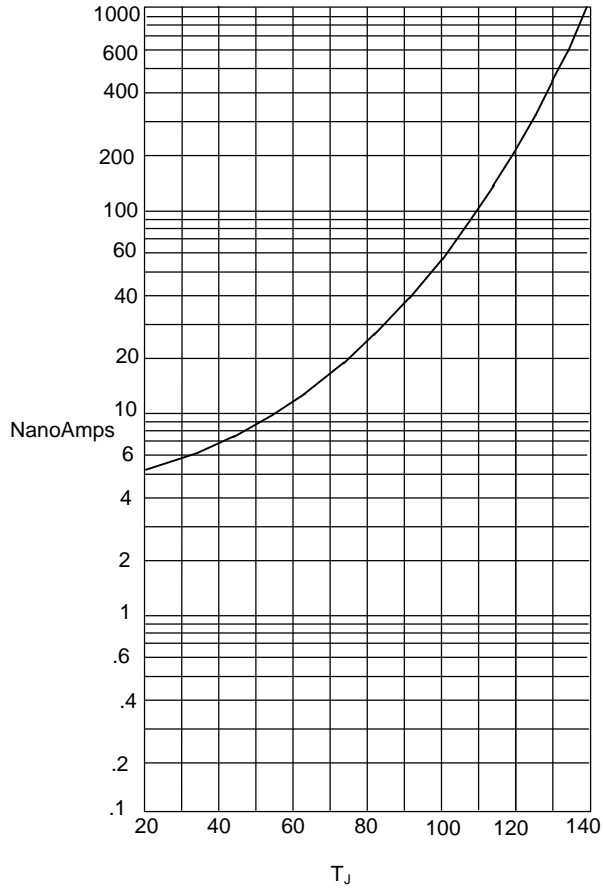
Figure 3  
Junction Capacitance



Junction Capacitance - pF versus  
Reverse Voltage - Volts

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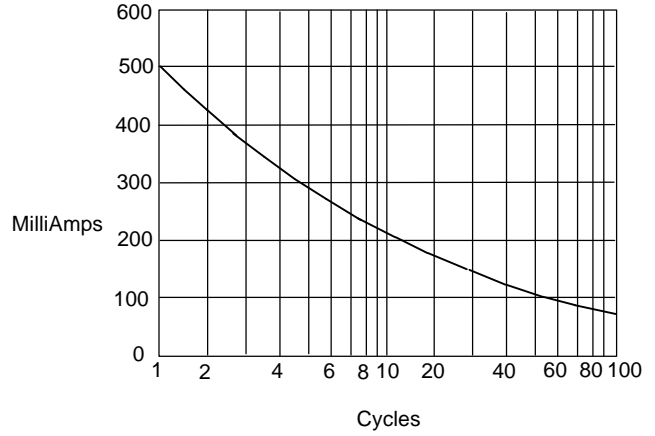
Figure 4  
Typical Reverse Characteristics



Instantaneous Reverse Leakage Current - NanoAmperes versus Junction Temperature - °C

T<sub>A</sub>=25°C  
T<sub>A</sub>=100°C

Figure 5  
Peak Forward Surge Current



Peak Forward Surge Current - Amperes versus Number Of Cycles At 60Hz - Cycles